

P-Channel 20 V (D-S) MOSFET

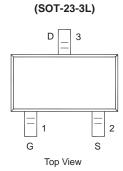
PRODUCT SUMMARY					
V _{DS} (V)	R _{DS(on)} (mΩ)(Typ.)	I _D (A) ^a	Q _g (Typ.)		
-20	19 at V _{GS} = -4.5 V	- 8	15 nC		
-20	25 at V _{GS} = -2.5 V	- 0			

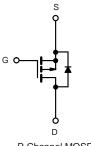
FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested

APPLICATIONS

- Power Management for Portable and Consumer
 - Load Switches
 - DC/DC Converters





P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (Γ _A = 25 °C, unle	ess otherwise r	noted)		
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	-20	V	
Gate-Source Voltage		V _{GS}	± 12	V	
Continuous Drain Current (T ₁ = 150 °C)	T _C = 25 °C	1	-8		
Continuous Drain Current (1j = 150°C)	T _C = 100 °C	I _D	-6	A	
Pulsed Drain Current		I _{DM}	-32		
Maximum Power Dissipation	T _C = 25 °C	Pn	2.5 ^{b, c}	w	
Maximum rower Dissipation	T _C = 100 °C	U I	1.2 ^{b, c}		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	つ °	
Soldering Recommendations (Peak Temperature)			260		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 s	R _{thJA}	-	82	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	-	2.2		

Notes:

a. $T_C = 25 \ ^{\circ}C.$

b. Surface mounted on 1" x 1" FR4 board.

c. t = 5 s.

d. Maximum under steady state conditions is 100 $^{\circ}\text{C/W}.$

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Parameter	Symbol Test Conditions		Min.	Тур.	Max.	Unit	
Static			<u> </u>				
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 20			V	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	- 0.4		-1.0	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 12 V$			± 10		
Zero Gate Voltage Drain Current		$V_{DS} = -20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			- 1	μA	
Zero Gale voltage Drain Current	IDSS	$V_{DS} = -20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 55 \text{ °C}$			- 10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le$ - 5 V, V_{GS} = - 4.5 V	- 8			Α	
Drain-Source On-State Resistance ^a		V _{GS} = - 4.5 V,I _D = - 5 A		19			
	R _{DS(on)}	V _{GS} = - 3.7 V, I _D = - 5 A 18			22	mΩ	
		V _{GS} = - 2.5 V, I _D = - 5 A		25	30		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 4.5 V,I _D = - 5 A		9		S	
Dynamic ^b							
Input Capacitance	C _{iss}			1340		pF	
Output Capacitance	C _{oss}	$V_{DS} = -10 V$, $V_{GS} = 0 V$, f = 1 MHz		156			
Reverse Transfer Capacitance	C _{rss}			126			
Total Gate Charge				15			
Gate-Source Charge	Q _{gs}	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -5 \text{ A}$		1.6		nC	
Gate-Drain Charge	Q_{gd}			2.8			
Gate Resistance	Rg	f = 1 MHz		11		Ω	
Turn-On Delay Time	t _{d(on)}			5			
Rise Time	t _r	V_{DD} = - 10 V, R_L = 10 Ω		11		ns	
Turn-Off DelayTime	t _{d(off)}	$I_D \cong$ - 5 A,V _{GEN} = - 4.5 V,R _g = 6 Ω		18		- 113	
Fall Time	t			5			
Drain-Source Body Diode Characteris	tics						
Continous Source-Drain Diode Current	۱ _S	T _C = 25 °C			-8	A	
Pulse Diode Forward Current	I _{SM}				-32		
Body Diode Voltage	V _{SD}	I _S = - 1 A, V _{GS} = 0 V		-0.6	-1.2	V	
Body Diode Reverse Recovery Time	t _{rr}			13	24	ns	
Body Diode Reverse Recovery Charge	Q _{rr}			7	15	nC	
Reverse Recovery Fall Time	ta	$I_F = -5 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, \text{T}_J = 25 \text{ °C}$		9		20	
Reverse Recovery Rise Time	t _b			7		ns	

Notes:

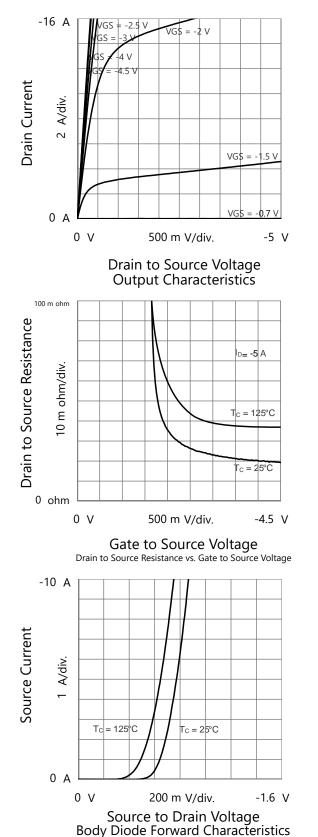
a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

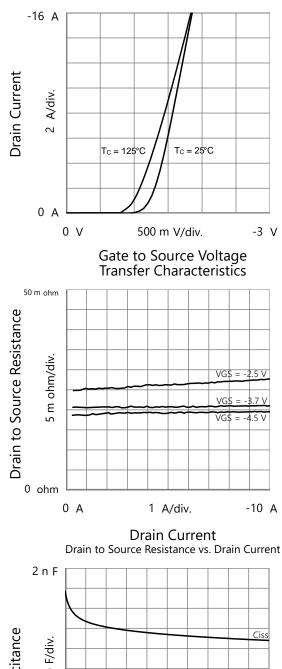
b. Guaranteed by design, not subject to production testing.

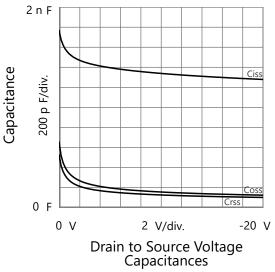
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)







4.5 V

0.45 V/div.

0 V

10 A

1 A/div.

0 A

Z_{⊌JA} Normalized Transient Thermal Resistance

0.001 1E-05

Source Current

Gate to Source Voltage

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Single Pulse

0.001

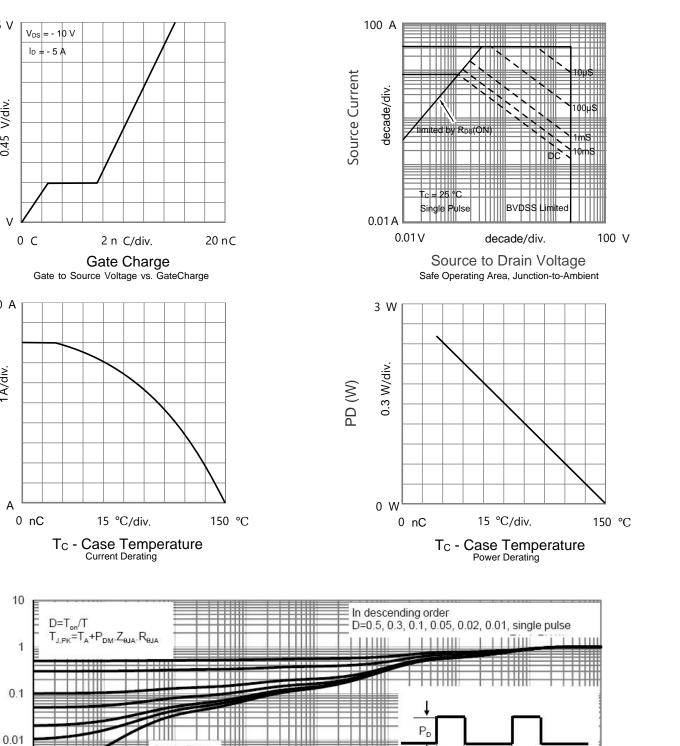
0.01

0.1

Pulse Width (s) Normalized Thermal Transient Impedance

TT

0.0001



Ť Tor

1

10

100

1000



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